

-40V P-CHANNEL Power MOSFET

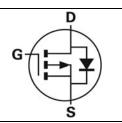
V<sub>DSS</sub>, -40V

 $R_{DS(ON)}$  ,  $50m\Omega$  (max.) @ VGS=-10V  $R_{DS(ON)}$  ,  $75m\Omega$  (max.) @ VGS=-4.5V

I<sub>D</sub> , -22.8A

#### TO-252





## Description

The SGP4038D is the highest performance trench P-Ch MOSFETs with extreme high cell density, which provide excellent  $R_{DS(ON)}$  and gate charge for most of the synchronous buck converter applications.

The SGP4038D meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

#### **Features**

- · Low On-Resistance
- Low Input Capacitance
- · Low Miller Charge
- Low Input/Output Leakage
- · Pb-free lead plating; RoHS compliant

#### **Applications**

- Motor / Body Load Control
- Automotive Systems
- Load Switch
- DC-DC converters and Off-line UPS

**Ordering Information** 

Ordering Code	RoHS Status	Package	Package Code	Packing	Quantity
SGP4038D	Halogen-Free	TO-252	D	Tape & Reel	2,500

Absolute Maximum Ratings (T<sub>A</sub>=25°C unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V <sub>DS</sub>	-40	V
Gate-Source Voltage		V <sub>G</sub> S	±20	V
Drain Current-Continuous	T <sub>C</sub> =25°C	L	-22.8	А
Drain Current-Continuous	T <sub>C</sub> =100°C	l <sub>D</sub>	-14.4	А
Drain Current-Pulsed Note 1		I <sub>DM</sub>	-50	А
Avalanche Current, L=0.1mH		las	-28	А
Avalanche Energy, L=0.1mH Note 3		Eas	39.2	mJ
Maximum Dawar Dissination	T <sub>C</sub> =25°C	D	41.7	W
Maximum Power Dissipation Tc=100°C		P <sub>D</sub>	16.7	W
Storage Temperature Range		T <sub>STG</sub>	-55 to +175	°C
Operating Junction Temperature Range		TJ	-55 to +175	°C

**Thermal Resistance Ratings** 

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Maximum Junction-to-Ambient Note 1	Reja	Steady State	-	=	62	°C/W
Maximum Junction-to-Case	Rejc	Steady State	-	-	3	°C/W

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# Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

OFF CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>DS</sub> =-250µA	-40	-	ī	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-32V, V <sub>GS</sub> =0V	-	-	-1	μΑ
Gate-Body Leakage	Igss	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA

ON CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>DS</sub> =-250µA	-1	-	-2.5	V
Drain-Source On-State Resistance	Б	V <sub>GS</sub> =-10V, I <sub>DS</sub> =-8A	-	35	50	mΩ
	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-4.5V, I <sub>DS</sub> =-5A	-	45	75	
Forward Transconductance Note 1	gfs	V <sub>DS</sub> =-5V, I <sub>D</sub> =-18A	-	12	-	S

DYNAMIC CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input Capacitance	Ciss		-	984	-	
Output Capacitance	Coss	V <sub>DS</sub> =-20V, V <sub>GS</sub> =0V, f=1MHz	-	105	-	pF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	78	-	

SWITCHING CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Turn-On Delay Time	$T_{d(on)}$		-	19	-	
Rise Time	tr	$V_{DD}$ =-20V, $V_{GS}$ =-10V, $R_{G}$ =3.3 $\Omega$ , $I_{D}$ =-18A	-	12.6	-	200
Turn-Off Delay Time	$T_{d(off)}$		-	47.6	-	ns
Fall Time	t <sub>f</sub>		-	4.5	-	
Total Gate Charge at 10V	Qg	\\ - 20\\ \\ - 4.5\\	-	8.8	-	
Gate to Source Gate Charge	$Q_{gs}$	$V_{DS}$ =-20V, $V_{GS}$ =-4.5V, $I_{D}$ =-18A	-	2.4	-	nC
Gate to Drain "Miller" Charge	$Q_{gd}$	1D10M	-	3	-	

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Diode Forward Voltage	$V_{SD}$	V <sub>GS</sub> =0V, I <sub>S</sub> =-18A	-	-	-1.2	V
Body Diode Reverse Recovery Time	Is	\/-=\/-=0\/ Force Current	-	-	-25	Α
Body Diode Reverse Recovery Charge	I <sub>SM</sub>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	-	-	-50	Α

#### Notes:

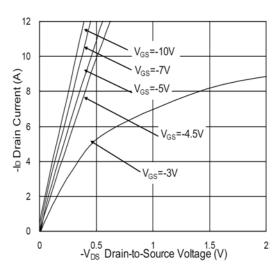
- 1. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 2. Reja is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Reja is guaranteed by design while Reca is determined by the user's board design. Reja shown below for single device operation on FR-4 in still air.
- 3. The EAS data shows Max. rating. The test condition is  $V_{DD}$ =-25V,  $V_{GS}$ =-10V, L=0.1mH,  $I_{AS}$ =-28A



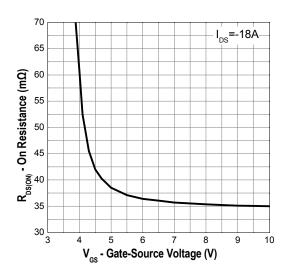
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# **Typical Operating Characteristics**

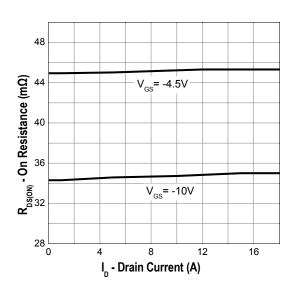
#### **Output Characteristics**



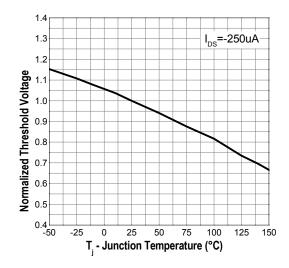
#### **Gate-Source On Resistance**



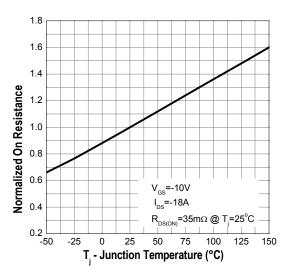
#### **Drain-Source On Resistance**



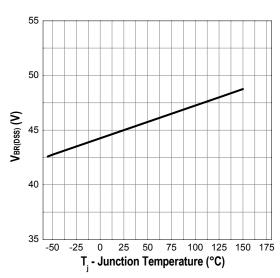
# **Gate Threshold Voltage**



#### **Drain-Source On Resistance**



## Source-Drain Diode Forward

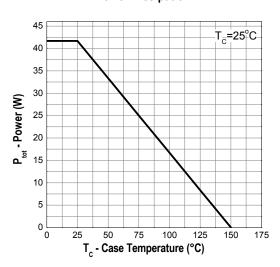




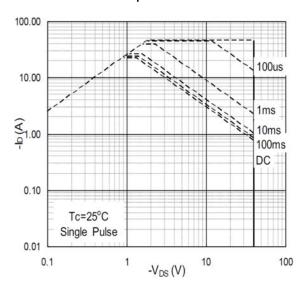
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# **Typical Operating Characteristics (Cont.)**

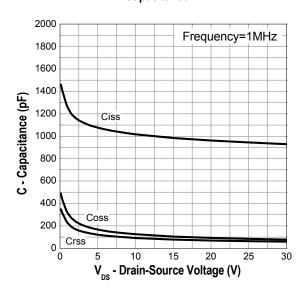
#### **Power Dissipation**



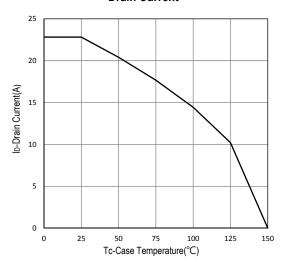
#### **Safe Operation Area**



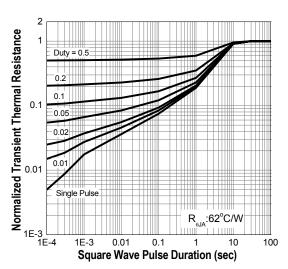
Capacitance



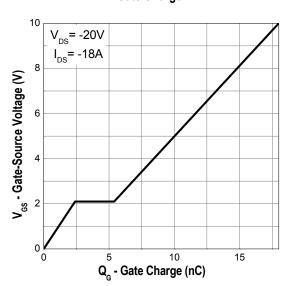
**Drain Current** 



**Transient Thermal Impedance** 



**Gate Charge** 





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# **Marking Information**

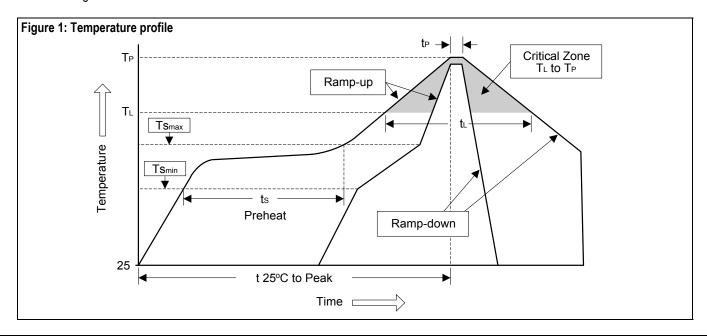
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SGP4038D  YYMMXXX  YY: Ye MM: M	: Date Code



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# Soldering Methods for Silicongear's Products

- 1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%
- 2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T <sub>L</sub> to T <sub>P</sub> )	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (Ts <sub>min</sub> )	100°C	150°C
- Temperature Max (Ts <sub>max</sub> )	150°C	200°C
- Time (min to max) (ts)	60 to 120 sec	60 to 180 sec
Tsmax to T∟		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T∟)	183°C	217°C
- Time (t <sub>L</sub> )	60 to 150 sec	60 to 150 sec
Peak Temperature (T <sub>P</sub> )	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak	10 to 20 ooo	20 to 40 coo
Temperature (t₂)	10 to 30 sec	20 to 40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec



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